



Panel Session: *Looking Forward, Looking Back*

**James C. Anderson
MIT Lincoln Laboratory**

**HPEC06
Wednesday, 20 September 2006**

This work is sponsored by DARPA/IPTO ACIP/PCA under Air Force Contract #FA8721-05-C-0002. Opinions, interpretations, conclusions and recommendations are those of the author and are not necessarily endorsed by the United States Government.

Reference to any specific commercial product, trade name, trademark or manufacturer does not constitute or imply endorsement.



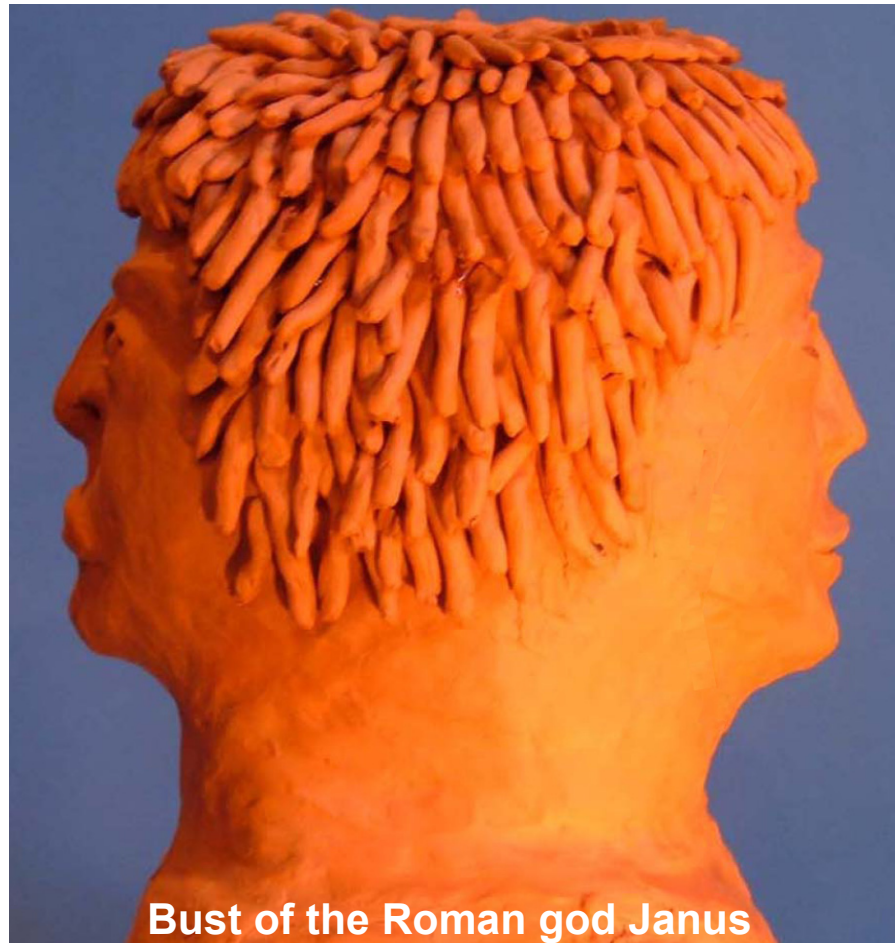
Objective & Schedule

- **Objective: using lessons learned from the last 10 yrs, project the next 10 yrs of HPEC technology & its impact on DoD systems**
- **Schedule**
 - ➔ – **1540-1600: Overview**
 - **1600-1605: Introduction of the panelists**
 - **1605-1620: Guest speaker Steve Poole**
 - **1620-1700: Previously-submitted questions for the panel**
 - **1700-1725: Open forum**
 - **1725-1730: Conclusions & the way ahead**



Looking Forward, Looking Back

**10 yrs
into the
past &
future, or
2006 \pm 1/2%**



Bust of the Roman god Janus

**20 min to
cover 20 yrs,
or 1% of time
since ancient
Rome!**

**How can we hope to make relevant analyses
& projections over such a time span?**



It Doesn't Get Any Better Than This

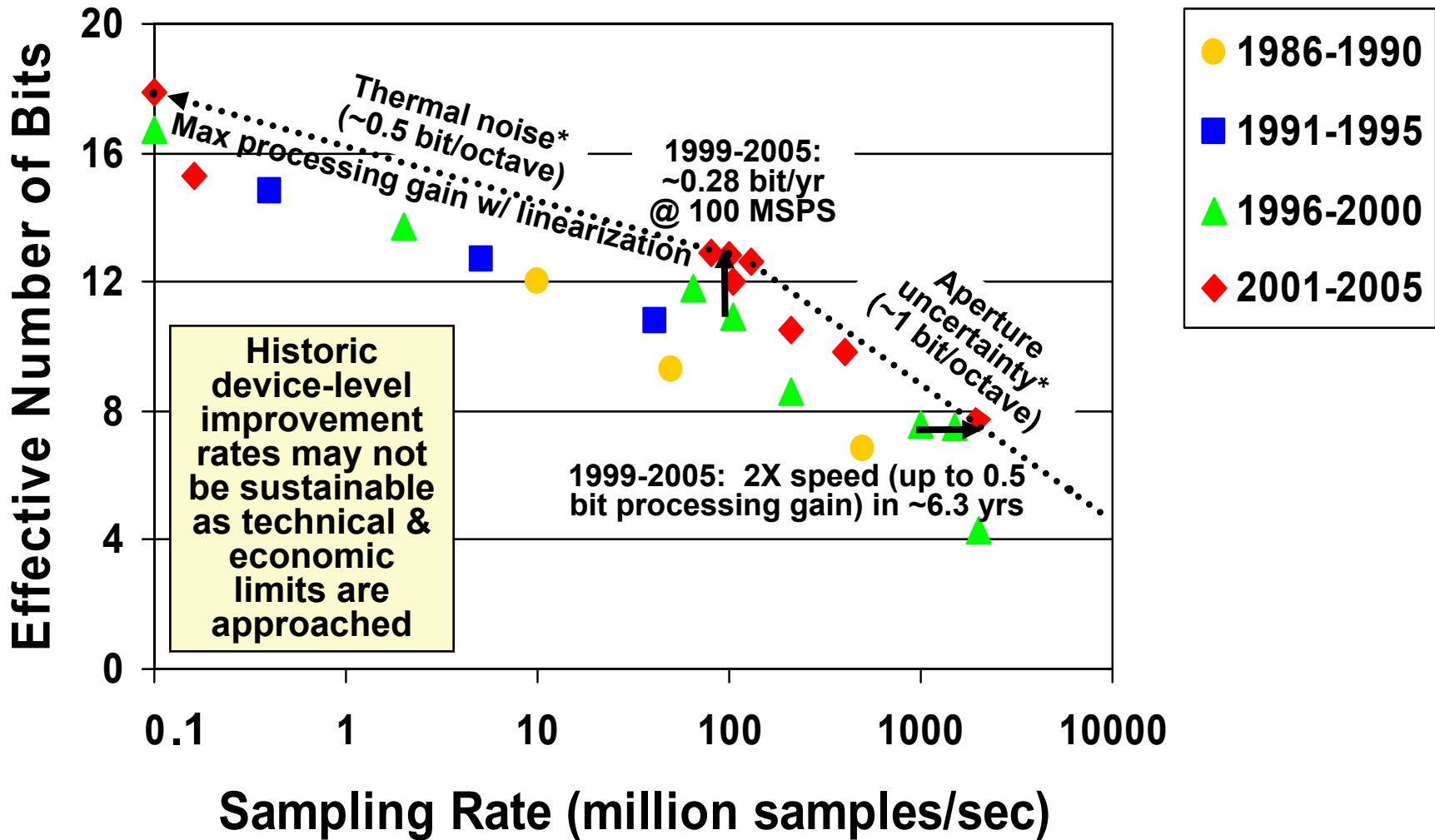
- **1995: smallest hearing aid battery**
 - So tiny that a dozen easily fit in volume of a U.S. nickel
 - Not likely to get any smaller (too difficult for elderly to handle)
- **1996: automotive toll-collection transponders**
 - Prototype systems developed by many major manufacturers (including Digital Equipment Corp., Raytheon & Texas Instruments)
 - No further improvements req'd after specs met
 - # of vehicles @ given speed in operating zone
 - Xpndr frequency, size, power, lifetime & reliability
- **2002: analog-to-digital converters for audio market**
 - 24-bit resolution (18 effective bits) & 40 KHz analog bandwidth
 - Approaches or exceeds limits of human hearing
 - Future improvements likely limited by thermal noise



Some problems get “solved,” and improvement rates may level off after key requirements are met



Highest-performance COTS (commercial off-the-shelf) ADCs (analog-to-digital converters), 1Q06



*Performance limiters shown are “design challenges” rather than “hard limits” (R.H. Walden, IEEE Jour. on Selected Areas in Comm., Apr. 1999)



Moore is Less

- “Original” Moore’s Law (1965, revised 1975):
4X transistors/chip every 3 yrs
- Improvements came from decreasing geometry, increasing chip size & “circuit cleverness”
- Held from late '70s - late '90s for memory chips

Projected 2000 Wafer, circa 1975



Moore was not always accurate

Slide #12 from Gordon Moore’s
“*No Exponential is Forever ...
but We Can Delay ‘Forever’*,”
ISSCC03, [www.intel.com/
technology/silicon/mooreslaw](http://www.intel.com/technology/silicon/mooreslaw)

Pre-Y2K improvement rate
was faster (lithography
improved frequently &
chip size grew)



Hardware Improvement Rate Has Slowed in the Last Decade

- 1997 Edition of the *National Technology Roadmap for Semiconductors* (NTRS97) projected μP improvements @ **4.7X every 3 yrs**
 - 2.8X density (transistors/area)
 - 1.2X chip size growth (300 mm² size in 1997 to 750 mm² in 2012)
 - 1.4X speed @ constant power
- 2005 Edition of the *International Technology Roadmap for Semiconductors* (ITRS05) projects μP improvements @ **3.2X every 3 yrs** (for FPGAs, ASICs & multi-core processors)
 - 2X density (limited by lithography improvement rate & partially driven by economics)
 - No chip size growth
 - Growth ceased ~1998
 - μP chip size @ 310 mm² or less through 2020
 - 1.6X speed @ constant power
- At present, improvements for general-purpose uni-processors with large on-chip cache may be limited to **2X every 3 yrs**

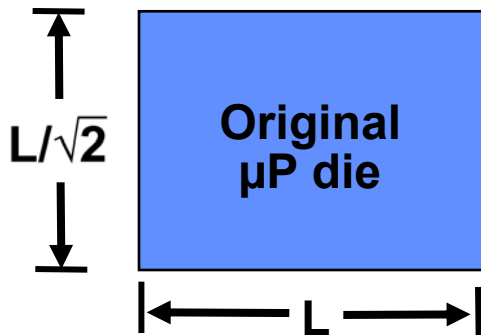
Latest projected improvement rate is still substantial, even if Improvement = $2^{\text{Years}/3}$



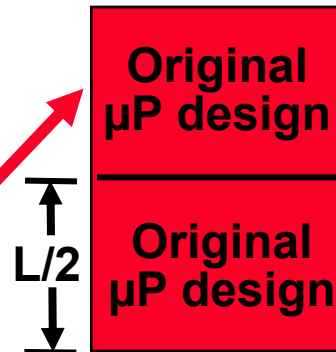
Microprocessor Family Improvement Rate Model

- Derived from ITRS05 projections
 - $1/\sqrt{2}$ geometry reduction every 3 yrs
 - Constant chip size & power

- Present-generation uni-processor



Re-implement
in new
geometry



- Next-generation dual-core chip

- 3X performance (2X transistors @ 1.5X speed, but 1/3 fewer bytes/OPS*)
- Incompatible HW/SW (2X pins, not a uni-processor)

Re-design
in new
geometry



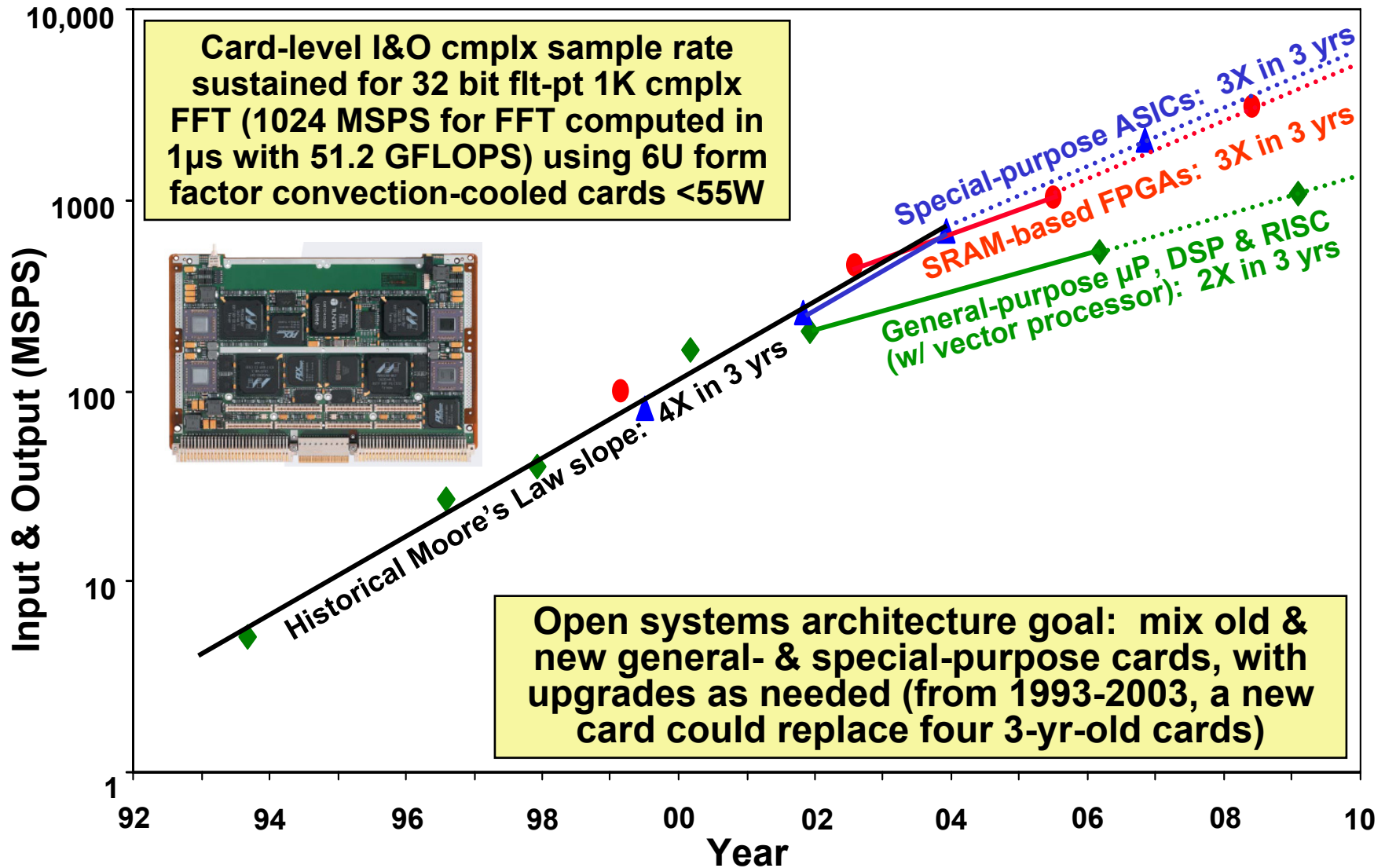
- Next-generation uni-processor

- 2X performance (2X transistors @ same speed, bytes/OPS* unchanged)
- Compatible HW/SW

*Operations per second, or “throughput”

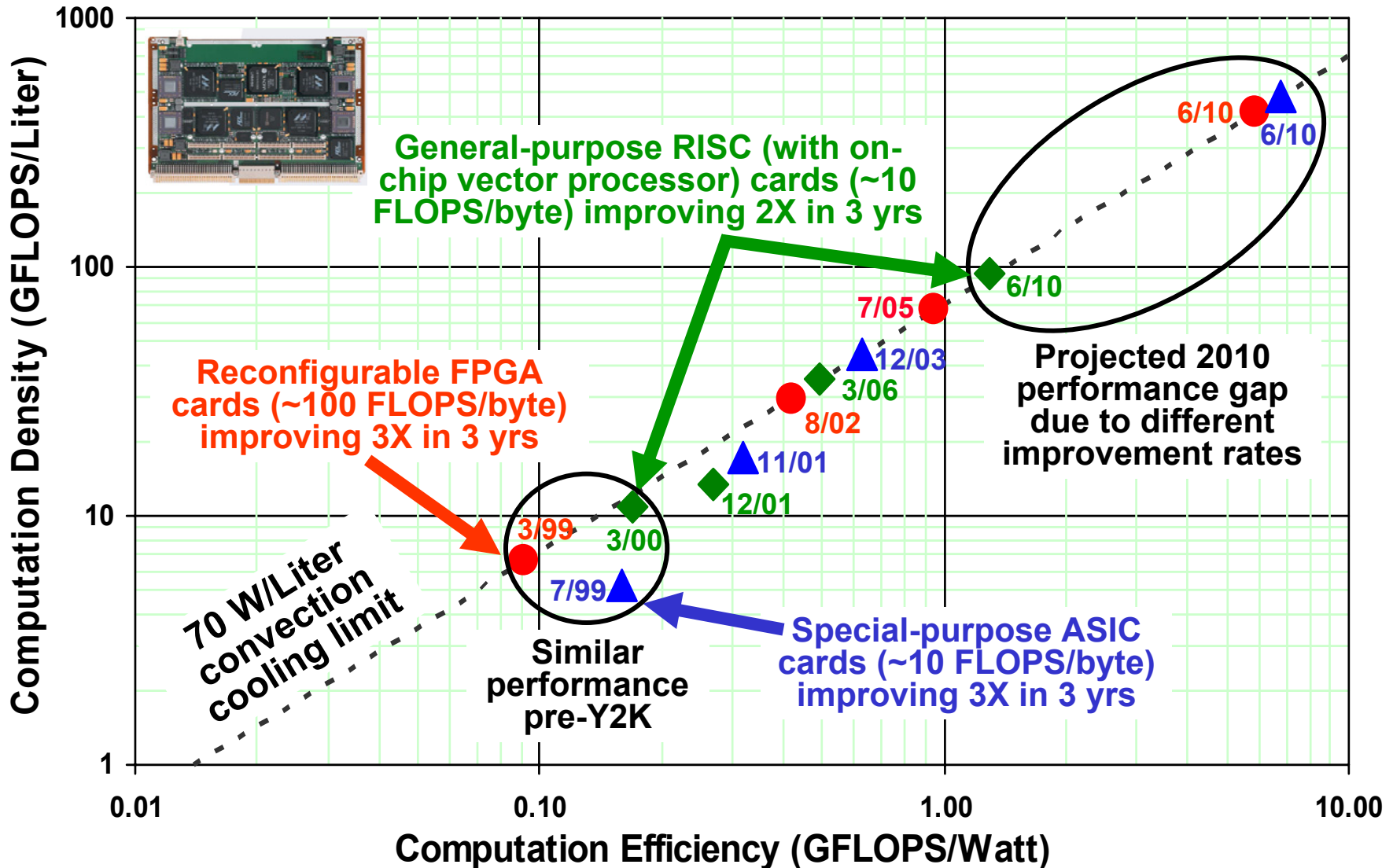


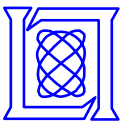
Timeline for Highest Performance COTS Multiprocessor Card Technologies, 3Q06



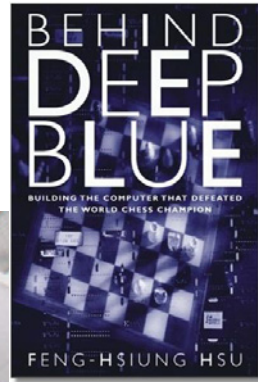


Improvements in COTS Embedded Multiprocessor Card Technologies, 3Q06





The Decades Beyond Deep Blue



- 5/97: Deep Blue beats chess champ Kasparov
 - Custom ASICs
 - Comparable to a computer with up to 40 trillion operations per second
 - 1270 kg



- 10/02: Deep Fritz ties chess champ Kramnik
- 1-2/03: Deep Junior ties former champ Kasparov
- Deep Fritz & Deep Junior are programs running on **general-purpose servers**
 - ~10,000 lines of C++
 - 15 billion instructions per second & 3 billion bytes of memory (5 IPS/byte)



Food for Thought

- Feasible ~2005
- Deep Dew hand-held chess champ
 - 0.6 L & 0.6 kg
 - 22W for 3.5 hrs (22 AA Li/FeS₂ cells)
 - COTS devices include voice recognition & response chip for I/O





More Food for Thought



- Feasible ~2005
- Deep Dew hand-held chess champ
 - 0.6 L & 0.6 kg
 - 22W for 3.5 hrs (22 AA Li/FeS₂ cells)
 - COTS devices include voice recognition & response chip for I/O



- 2008: Deep Yogurt based on improved Deep Dew design
 - 1/3 the size & power
 - 3X improvement in 3 yrs



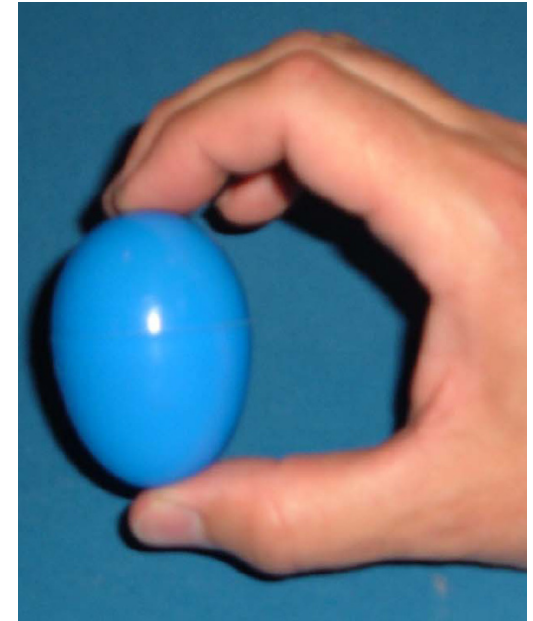
Still More Food for Thought



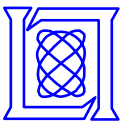
- Feasible ~2005
- Deep Dew hand-held chess champ
 - 0.6 L & 0.6 kg
 - 22W for 3.5 hrs (22 AA Li/FeS₂ cells)
 - COTS devices include voice recognition & response chip for I/O



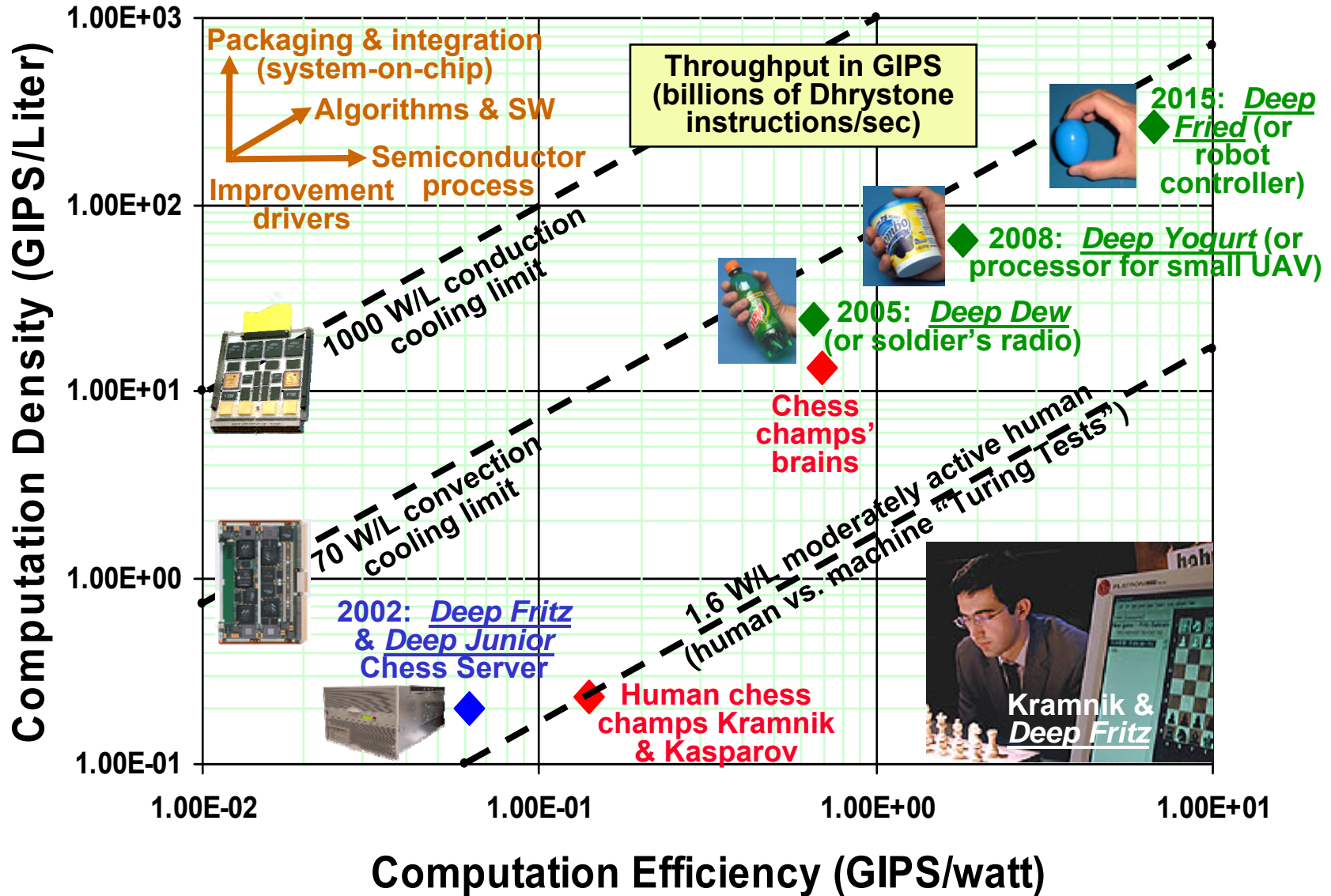
- 2008: Deep Yogurt based on improved Deep Dew design
 - 1/3 the size & power
 - 3X improvement in 3 yrs



- 2015: Deep Fried has challenging weight & form factor constraints
 - I/O via accelerometer & vibrating motor
 - Unaided hens already beat humans at tic-tac-toe



Power per Unit Volume (Watts/Liter) for Representative Systems, 2002-2015





Objective & Schedule

- **Objective: using lessons learned from the last 10 yrs, project the next 10 yrs of HPEC technology & its impact on DoD systems**
- **Schedule**
 - 1540-1600: Overview
 - – 1600-1605: Introduction of the panelists
 - 1605-1620: Guest speaker Steve Poole
 - 1620-1700: Previously-submitted questions for the panel
 - 1700-1725: Open forum
 - 1725-1730: Conclusions & the way ahead



Looking Forward, Looking Back Panelists

- **Dr. James C. Anderson, MIT Lincoln Laboratory (moderator)**
- **Mr. Jerry Oesterheld, SimVentions**
- **Mr. Richard Ridgley, National Reconnaissance Office**
- **Dr. Gary Shaw, MIT Lincoln Laboratory**
- **Mr. Stephen Poole, Oak Ridge National Laboratory & Los Alamos National Laboratory**

Panel members & audience may hold diverse, evolving opinions



Objective & Schedule

- **Objective: using lessons learned from the last 10 yrs, project the next 10 yrs of HPEC technology & its impact on DoD systems**
- **Schedule**
 - 1540-1600: Overview
 - 1600-1605: Introduction of the panelists
 - 1605-1620: Guest speaker Steve Poole
 - 1620-1700: Previously-submitted questions for the panel
 - 1700-1725: Open forum
 - ➔ – 1725-1730: Conclusions & the way ahead



Conclusions & The Way Ahead

- **In areas where many problems have been “solved” during the last decade, little progress is expected during the next decade**
- **Although there has been an improvement rate slowdown vs. historical Moore’s Law, the rate is still substantial**
- **Due to the slowdown, advanced packaging technology has increased importance in applications requiring high computation density**

The coming decade will see applications that are not yet on anybody’s drawing boards!



Backup Slides



1997 National Technology Roadmap for Semiconductors & 2005 International Technology Roadmap for Semiconductors

NTRS97

Year of 1st product shipment	1997	2003	2006	2009	2012	
DRAM half-pitch, nm	250	130	100	70	50	
Mbits per sq cm	96	x2.83 770	x2.86= 2200	x2.77= 6100	x2.79= 17,000	Avg: x2.82
Allowable max pwr, high-performance, W	70	130	160	170	175	
On-chip clock, MHz	750	2100	3500	6000	10,000	
Clock freq, MHz, for 70W power	750	x1.23 1131	x1.35= 1531	x1.61= 2471	x1.62= 4000	Avg: x1.41
Chip size (mm ²)	300	x1.2 430	x1.2= 520	x1.2= 620	x1.2= 750	Avg: x1.2
Max improvement: density x size x speed@70W		x4.18 x4.18	x4.63	x5.35	x5.42	Avg: x4.77

ITRS05

Year of production	2006	2009	2012	2015
DRAM half-pitch, nm	70	50	36	25
Mxstrs per sq cm	283	x2.00= 566	x2.00= 1133	x2.00= 2265
Allowable max pwr, high-performance, W	180	198	198	198
On-chip clock, MHz	6783	12,369	20,065	33,403
Clock freq, MHz, for 70W power	2638	x1.66= 4373	x1.62= 7094	x1.66= 11,810
Chip size (mm ²)	195	x1= 195	x1= 195	x1= 195
Max improvement: density x size x speed@70W		x3.32	x3.24	x3.32 Avg: x3.29



Representative 90nm Devices ca. 2006

- **μP: Freescale MPC7448 PowerPC**
 - 10W @ 1.4 GHz
 - 11.2 GFLOPS peak (**1.1 GFLOPS/W peak for chip alone**), single-precision
 - 1088 Kbytes on-chip memory (10K FLOPS/byte)
- **IBM Cell Broadband Engine**
 - 100W (est.) @ 3.0 GHz
 - 192 GFLOPS peak (**1.9 GFLOPS/W peak, est., for chip alone**), single-precision
 - 2592 Kbytes on-chip memory (74K FLOPS/byte)
- **FPGA: Xilinx Virtex-4 LX200**
 - 54W (est.) @ 225 MHz core & 375 MHz I/O (2 devices with external memory & I/O on 6U card)
 - 51.2 GFLOPS sustained (**0.95 GFLOPS/W sustained, est., for complete card**), single-precision
 - 528 Mbytes DDR-SRAM on card (97 FLOPS/byte)

Although Cell has greater computation efficiency (operations per watt), PowerPC has more on-chip memory for a given throughput



Representative COTS Primary (non-rechargeable) Cells

Type	Chemistry	Nominal/ cutoff voltage (volts)	Nominal energy (watt- hours)	Weight (grams)	Gravimetric energy density (Wh/kg)	Volume (cubic cm)	Volumetric energy density (Wh/Liter)	High-drain capability (constant power)
Zinc air 675-size (non- stackable) hearing aid	Zinc air (Zn/O ₂)	1.4/1.1	0.66	1.85	357	0.57	1150	Poor: 15 mW max. (12 mA limiting current)
Alkaline C-size flashlight	Zinc manganese dioxide (Zn/MnO ₂)	1.5/0.8	8.3	64	131	26	323	Good: 1W for 3.6 hrs (0.324Ω internal resistance when fresh)
Lithium AAA-size (AA-size) digital camera	Lithium iron disulfide (Li/FeS ₂)	1.5/1.0	1.5 (3.6)	7.6 (14.5)	200 (250)	3.8 (8)	400 (453)	Good: 0.5W (1W) for 3 (3.6) hrs w/ 2A limiting current

Zinc air has high energy density but limited current, alkaline has lowest cost, lithium has best performance (& low self-heating) for high-drain applications



ADC Database (printable notes page) for “Highest-performance COTS (commercial off-the-shelf) ADCs (analog-to-digital converters), 1Q06”

James C. Anderson, JCA@LL.MIT.EDU, 1/6/06; non-proprietary vendor data from analog-to-digital converter historical database dated 1/6/06.

When a value for the effective number of bits (ENOB) has not been provided by the manufacturer, one has been calculated using the approximation $ENOB = (SINAD - 1.76)/6.02$, where SINAD is the signal to noise-and-distortion ratio (typically expressed in dB relative to a nearly full-scale sine wave input having a frequency nearly half the sampling rate). Energy required for each effective quantization level is $EQ = Power / [(2^{ENOB}) \times (\text{sampling rate})]$, and includes on-chip de-multiplexer if any.

1986-1990:

10 MSPS 14-bit (ENOB=12.0) 10/90 Analog Devices AD9014, SINAD=-74dB, SFDR=87dB, 12.8W, EQ=310pJ; 2 ECL hybrid DIPS on small PCB
50 MSPS 10-bit (ENOB=9.3) 10/88 SPT (Honeywell) HADC77600, SINAD=-58dB, SFDR unknown, 4.7W, EQ=150pJ; 1.2um bipolar monolithic flash
500 MSPS 8-bit (ENOB=6.8) 1/89 Tektronix TKAD10C, SINAD=42.7dB, SFDR unknown, 7.5W, EQ=130pJ; hybrid DIP, 1:2 DMUX (250 MSPS matched ping-pong)

1991-1995:

400 KSPS 16-bit (ENOB=14.8) 7/92 Analog Devices AD1382, SINAD=91dB, SFDR=85dB, 2.8W, EQ=250pJ; hybrid DIP, 500 KSPS max.
5.12 MSPS 14-bit (ENOB=12.7) 11/92 Burr-Brown ADC614LH, SINAD=78dB, SFDR=90dB, 6.1W, EQ=180pJ; ECL hybrid DIP
41 MSPS 12-bit (ENOB=10.8) 4/95 Analog Devices AD9042, SINAD=67dB, SFDR=80dB, 0.6W, EQ=8pJ; high-speed complementary bipolar (XCFB)

1996-2000:

80 KSPS 24-bit (ENOB=16.8) 4/00 AKM AK5393, SINAD=103dB, SFDR=117dB, 0.47W, EQ=26; 2-ch delta-sigma with on-chip filters & 96 KSPS output
2 MSPS 16-bit (ENOB=13.7) 11/98 Analog Devices AD9260, SINAD=84.5dB, SFDR=105dB, 0.61W, EQ=22pJ; CMOS, 20 MHz clock & 2.5 MSPS output
65 MSPS 14-bit (ENOB=11.8) 10/99 Analog Devices AD6644, SINAD=73dB, SFDR=85dB, 1.3W, EQ=5.6; high-speed complementary bipolar (XCFB)
105 MSPS 12-bit (ENOB=10.9) 3/99 Analog Devices AD9432-105, SINAD=66.7, SFDR=80dB, 0.85W, EQ=4.2; BiCMOS
210 MSPS 10-bit (ENOB=8.6) 10/00 Analog Devices AD9410, SINAD=52.5dB, SFDR=58dB, 2.1W, EQ=26pJ; BiCMOS, 1:2 DMUX
1 GSPS 8-bit (ENOB=7.55) 5/99 Maxim MAX104, SINAD=46.2, SFDR=52.3, 5.25W, EQ=28pJ; bipolar, 1:2 DMUX
1.5 GSPS 8-bit (ENOB=7.53) 8/00 Maxim MAX108, SINAD=46.1dB, SFDR=54.1dB, 5.3W, EQ=19; bipolar, 1:2 DMUX
2 GSPS 8-bit (ENOB=4.3) 3/98 Rockwell RSC-ADC080E, SINAD=27.5dB, SFDR=30dB, 5W, EQ=130pJ; bipolar, Gray code output

2001-2005:

80 KSPS 24-bit (ENOB=18.0) 7/02 AKM AK5394A, SINAD=110dB, SFDR=120dB, 0.67W, EQ=16; 2-ch delta-sigma with on-chip filters & 96 KSPS output
160 KSPS 24-bit (ENOB=15.3) 7/02 AKM AK5394A, SINAD=94dB, SFDR=120dB, 0.67W, EQ=52; 2-ch delta-sigma with on-chip filters & 192 KSPS output
80 MSPS 16-bit (ENOB=12.9) 12/03 Analog Devices AD10678, SINAD=79.7dB, SFDR=94.2dB, 6.9W, EQ=11pJ; PCB w/ quad 14-bit ADCs & digital post-processing
100 MSPS 16-bit (ENOB=12.8) 12/05 Analog Devices AD9446-100, SINAD=78dB, SFDR=89dB, 3.6W, EQ=3.6pJ

(up to 0.5 bit/octave processing gain could provide 5 additional bits, for ENOB=17.8, at a 97.7 KSPS effective sampling rate)

105 MSPS 14-bit (ENOB=12.0) 7/03 Analog Devices AD6645-105, SINAD=74dB, SFDR=89dB, 1.5W, EQ=3.5pJ; high-speed complementary bipolar (XCFB)
130 MSPS 16-bit (ENOB=12.6) 9/05 Linear Technology LTC2208, SINAD=77.4dB, SFDR=90dB, 1.25W, EQ=1.6pJ; 1:2 DMUX, optional dither
210 MSPS 12-bit (ENOB=10.5) 7/03 Analog Devices AD9430-210, SINAD=64.5dB, SFDR=77dB, 1.3W, EQ=4.3pJ; BiCMOS, 1:2 DMUX
400 MSPS 12-bit (ENOB=9.8) 3/03 Analog Devices AD12400, SINAD=61dB, SFDR=71dB, 7W, EQ=19pJ; module w/ dual 12-bit ADCs & digital post-processing
2 GSPS 10-bit (ENOB=7.8) 9/05 Atmel-Grenoble AT84AS004, SINAD=49dB, SFDR=55dB, 6.5W, EQ=15; 1:4 DMUX

100 MSPS high-resolution improvement rate: AD9432-105 (3/99, ENOB=10.9) vs. AD9446-100 (12/05, ENOB=12.8) gives 1.9 bits in 82 mos.

8/10-bit (ENOB=-7.7) high-speed improvement rate: MAX104 (5/99, 1 GSPS) vs. AT84AS004 (9/05, 2 GSPS) gives 2X in 76 mos.

Performance limiters based on selected values from Fig. 7 of Robert H. Walden’s “Analog-to-Digital Converter Survey and Analysis,” IEEE Journal on Selected Areas in Communications, Vol. 17, No. 4, April 1999, pp. 539-550. These should be considered as “design challenges” rather than “hard limits.” For example, the thermal noise can be reduced by reducing the effective resistance or temperature, but at additional cost.

Thermal noise (2000 ohms): 17.8 bits @ 0.1 MSPS & 12.5 bits @ 100 MSPS for 5.3 bits drop-off in 3 decades = 10 octaves. Verification: this curve matches the max. processing gain with linearization curve for the AD9446-100, which is another way to effectively “create” an ADC having lower sampling rate.

Aperture uncertainty (0.2 ps): 13 bits @ 100 MSPS & 8.5 bits @ 2.3 GSPS for 4.5 bits drop-off in ~4.5 octaves. Verification: LTC2208 (ENOB=12.6 @ 130 MSPS) vs. Agilent Infinium DSO80000 (ENOB=4.6 @ 6 GHz & 20 GSPS, with equivalent sampling rate = 12 GSPS) gives 8 bits in ~7 octaves, and this result is consistent with Rockwell Scientific RAD006 (ENOB>5.5 @ 6 GSPS).